

# **Excellent Integrated System Limited**

Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-4EGH06-M3/5BT</u>

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Datasheet of VS-4EGH06-M3/5BT - DIODE FRED 600V 4A SMB

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### **VS-4EGH06-M3**

HALOGEN

FREE

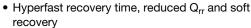
Vishay Semiconductors

# Hyperfast Rectifier, 4 A FRED Pt®



PRODUCT SUMMARY				
Package	DO-214AA (SMB)			
I <sub>F(AV)</sub>	4 A			
$V_{R}$	600 V			
V <sub>F</sub> at I <sub>F</sub>	1.2 V			
t <sub>rr</sub> typ.	30 ns			
T <sub>J</sub> max.	175 °C			
Diode variation	Single die			

#### **FEATURES**







Low forward voltage drop

· Low leakage current

 Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

• Designed and qualified according to JEDEC®-JESD 47

 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	$V_{RRM}$		600	V	
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>L</sub> = 76 °C <sup>(1)</sup>	4	V	
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	55	Α	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	

#### Note

(1) Mounted on PCB with minimum pad size

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$	Ι <sub>R</sub> = 100 μΑ	600	-	-	
Forward voltage	VF	I <sub>F</sub> = 4 A	-	1.6	1.95	V
Forward voltage	VF	I <sub>F</sub> = 4 A, T <sub>J</sub> = 150 °C	-	1.2	1.4	
Reverse leakage current I <sub>R</sub>	$V_R = V_R$ rated	-	-	3		
	$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	-	100	μΑ	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	5.7	1	pF

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### **VS-4EGH06-M3**

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A/}\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	30	-	
Reverse recovery time t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	35	-		
	t <sub>rr</sub>	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	35	ns
	T <sub>J</sub> = 25 °C		-	22	-		
	T <sub>J</sub> = 125 °C		-	37	-		
Dook room ourrent		T <sub>J</sub> = 25 °C	$I_F = 4 A$	-	3.4	-	Α
Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 390 V	-	5.2	-	A	
Reverse recovery charge Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	40	-	nC	
	T <sub>J</sub> = 125 °C		-	103	-		

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistance, junction to case	R <sub>thJC</sub> <sup>(1)</sup>		-	-	18	°C/W
Thermal resistance, junction to ambient	R <sub>thJA</sub> <sup>(1)</sup>		-	-	90	C/ <b>VV</b>
Approximate Weight				0.1		g
Approximate Weight				0.003		OZ.
Marking device		Case style DO-214AA (SMB)		41	<del>1</del> 6	

#### Note

<sup>(1)</sup> Mounted on PCB with minimum pad size

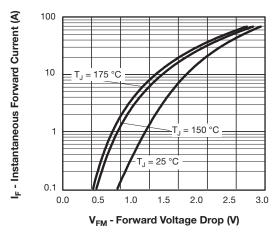


Fig. 1 - Typical Forward Voltage Drop Characteristics

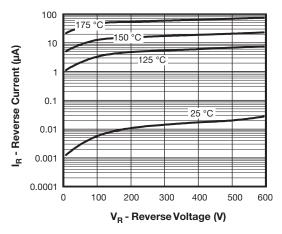


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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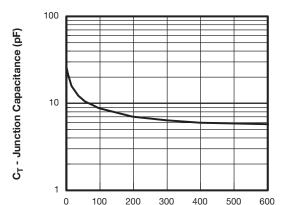
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V<sub>R</sub> - Reverse Voltage (V)
Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

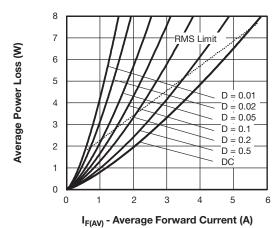


Fig. 5 - Forward Power Loss Characteristics

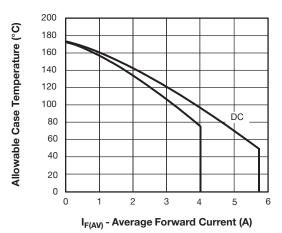


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

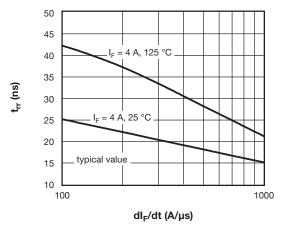


Fig. 6 - Typical Reverse Recovery vs. dl<sub>F</sub>/dt

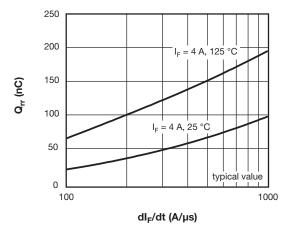


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

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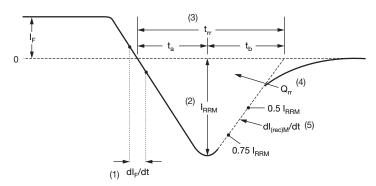
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- dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm l_F$  to point where a line passing through 0.75  $\rm l_{RBM}$  and 0.50  $\rm l_{RBM}$  extrapolated to zero current.
- (4)  $\ensuremath{\text{Q}_{\text{rr}}}$  area under curve defined by  $\ensuremath{t_{\text{rr}}}$  and  $\ensuremath{\ensuremath{I_{\text{BBM}}}}$

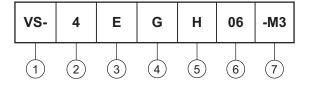
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 8 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

**Device code** 



- Vishay Semiconductors product
- 2 Current rating (4 = 4 A)
- 3 Circuit configuration:

E = single diode

4 - G = SMB package

5 - Process type,

H = hyperfast recovery

6 - Voltage code (06 = 600 V)

7 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION					
VS-4EGH06-M3/5BT	5BT	3200	13"diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95401</u>				
Part marking information	www.vishay.com/doc?95472			
Packaging information	www.vishay.com/doc?95404			

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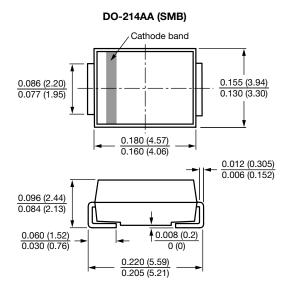


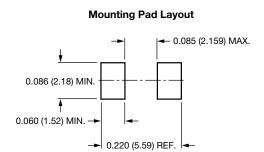
### **Outline Dimensions**

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### **SMB**

#### **DIMENSIONS** in inches (millimeters)







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